

*Substitute Abstract*

--ABSTRACT

B1 A film acoustic wave device having similar properties are obtained by changing at least one of the length and/or the width of upper electrodes; the distance between the upper electrodes; the length and/or the width of connecting patterns; the areas of bonding pads; and the pattern shape for the film acoustic wave device such as the area of capacitor electrodes electrically connected to the bonding pads. Property variations of the film acoustic wave devices caused from the positioning at a wafer is compensated for.--